### **Power Amplifiers (1/2)**

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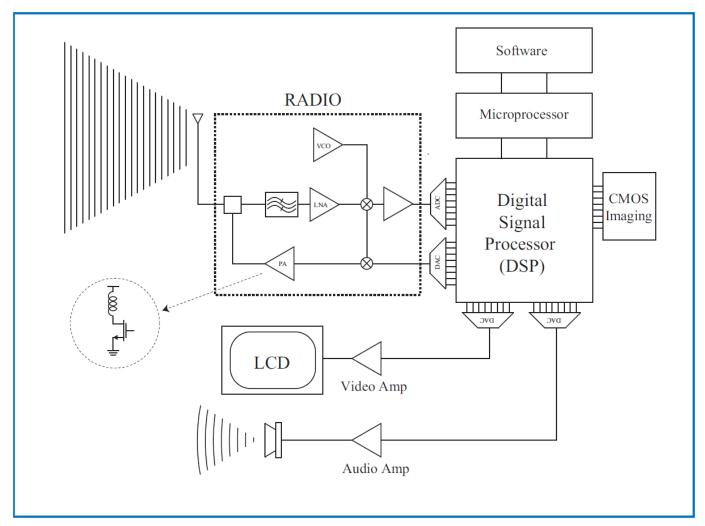
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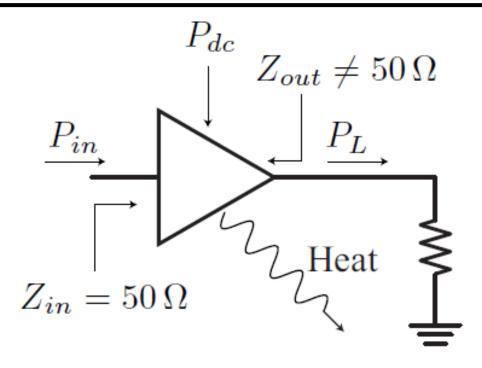


### **A Cell Phone**



[Ali Niknejad, EE142 &EE242 of UC Berkeley]

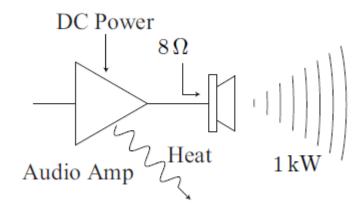
# **Power Amplifier (PA)**



- □Powerful: PA delivers power to a given load with maximum efficiency
- □Linear: PA faithfully transfers the modulation from the input to the output

[Ali Niknejad, EE142&EE242 of UC Berkeley]

# **Audio PA Example**



- □Consider a PA that delivers 1kW of power into 8 speakers.
- □Assuming a sinusoidal input, the peak voltage and current are

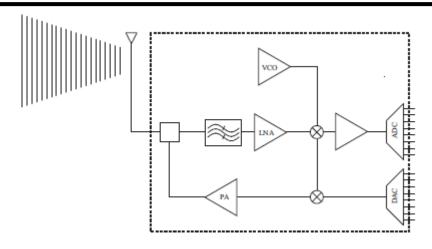
$$V = \sqrt{2RP} = \sqrt{2 \cdot 8 \cdot 1000} = 126V$$

$$I = \frac{2P}{V} = 15.8A$$

□Such large currents and voltages require special techniques

[Ali Niknejad, EE142&EE242 of UC Berkeley]

### **Mobile Phone Example**



□Consider a typical mobile phone that delivers 1W in to a 50 antenna. Here we find that

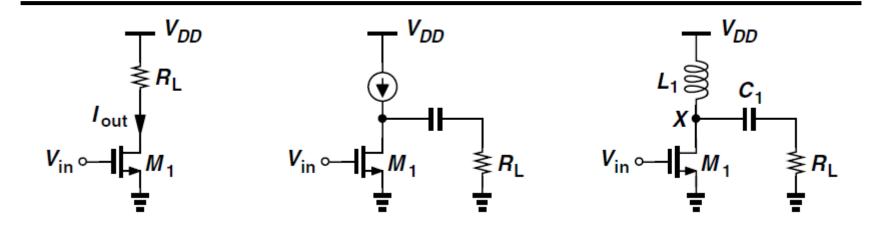
$$V_0 = \sqrt{2PR} = \sqrt{2 \cdot 50} = 10V$$

$$I_0 = 2/10 = 0.2$$
A

□Most high-frequency Si transistors cannot handle 10V due to breakdown. Thus we need to transform the voltage down to a safe value

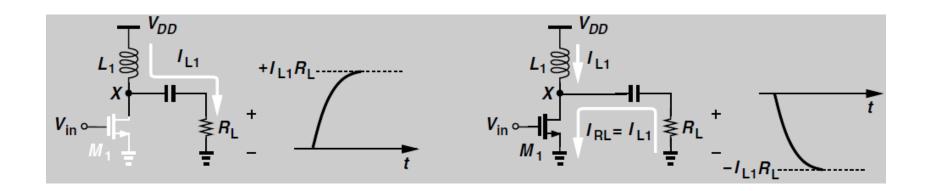
[Ali Niknejad, EE142&EE242 of UC Berkeley]

### **CS Stages**



- □Without an inductor, the circuits require a supply voltage greater than 10V
- $\Box$ If the load is realized as an inductor, the drain AC voltage exceeds the supply  $V_{DD}$ , even reaching  $2V_{DD}$  (or higher)
- □While allowing a lower supply voltage, the inductive load does not relax the "stress" on the transistor

### **CS Stages**



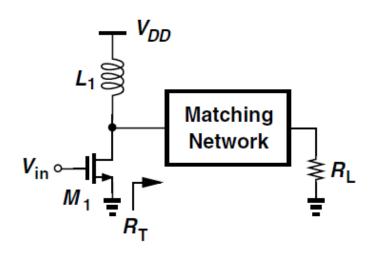
- □A fundamental issue in PA design: The trade-off between the output power and the voltage swing experienced by the output transistor
- □The product of the breakdown voltage and f<sub>T</sub> of silicon devices is around 200 GHz · V

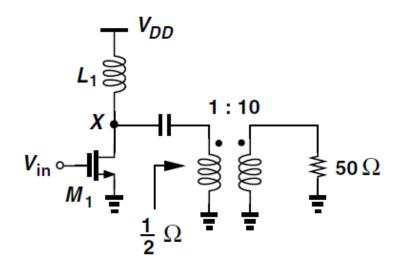
#### **PA Considerations**

- □PAs drive large voltages/currents into small load impedances. Thus matching networks are critical. Any loss in the matching network has a severe impact on the efficiency of the amplifier.
- □ Heat generation is high. We need to carefully provide heat sinks to keep the junction temperatures as low as possible.
- □ Due to the interface with the external "off-chip" world, packaging and board parasitics are very important.
- □The spectral "leakage" and harmonic generation in a PA must be kept to the a minimum in order to minimize interference to other users.

  [Ali Niknejad, EE142&EE242 of UC Berkeley]

### **Impedance Transformation**

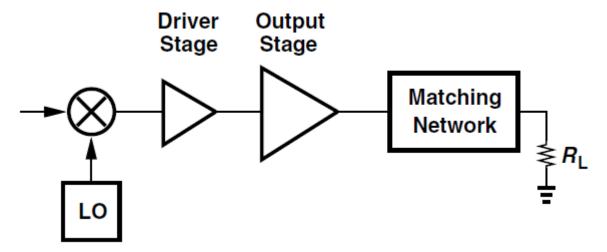




- $\Box$ The network transfers the load resistance to a lower value (R<sub>T</sub>) so that smaller voltage swings still deliver the required power
- □The need for transforming the voltage swings means that the current generated by the output transistor must be proportionally higher

### **Effect of High Current**

□If the output transistor is chosen wide enough to carry a large current, then its input capacitance is very large, making the design of the preceding stage difficult



- □Tapered stages can be interposed between the upconversion mixers and the output stage
- ☐ The multiple stages tend to limit TX output compression point
- ☐ The driver also consumes high power

# **Efficiency**

□The Power Added Efficiency, or PAE, is a measure of how much power is added to a signal normalized by the DC power consumption  $P_L - P_{in}$ 

 $PAE = \eta = \frac{P_L - P_{in}}{P_{dc}}$ 

□If the power gain is large

$$PAE = \frac{P_L(1 - G_p^{-1})}{P_{dc}} \approx \frac{P_L}{P_{dc}}$$

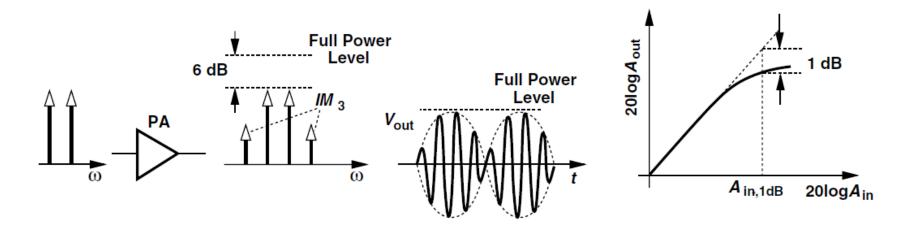
□The drain efficiency is defined as

$$\eta_{c|d} = \frac{P_L}{P_{dc}}$$

[Ali Niknejad, EE142&EE242 of UC Berkeley]

# Linearity

□PA nonlinearity leads to: 1) high adjacent channel power as a result of spectral regrowth, and 2) amplitude compression

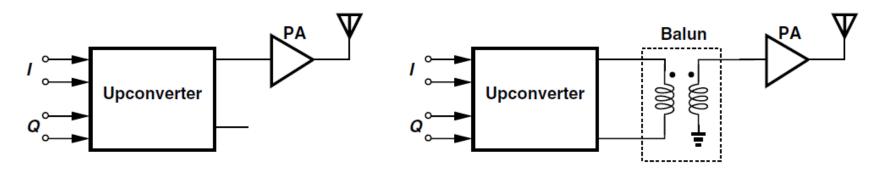


□The amplitude of the tones is chosen such that each main component at the output is 6 dB below the full power level, thus producing the maximum desired output voltage swing when the two tones add in-phase

[B. Razavi, RF Microelectronics]

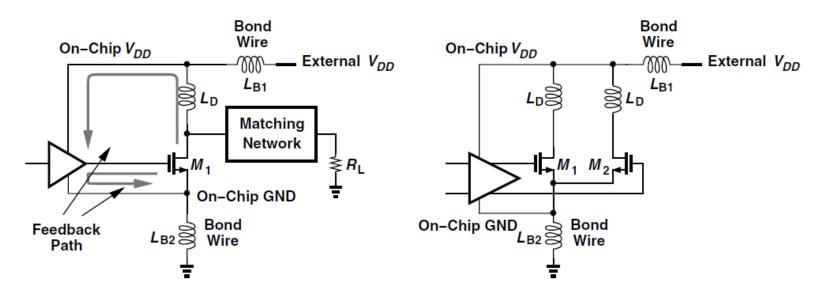
# Single Ended and Differential

- □The antenna is typically single-ended, and single-ended RF circuits are much simpler to test
- □Single-ended transmitter "waste" half of the voltage gain because they sense only one output of the upconverter



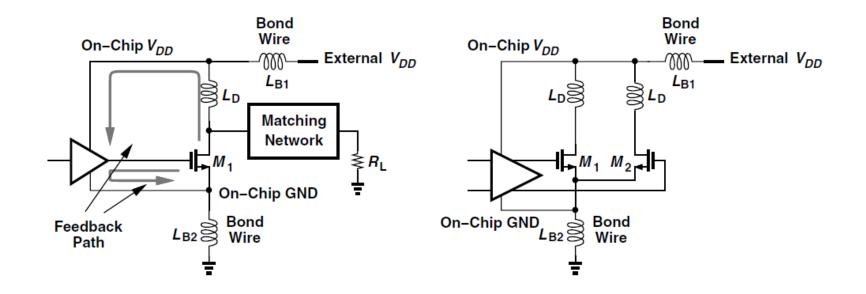
- □ A balun can be interposed between upconverter and PA
- □But the balun introduces its own loss, especially if it is integrated on the chip

#### **Bond Wires**



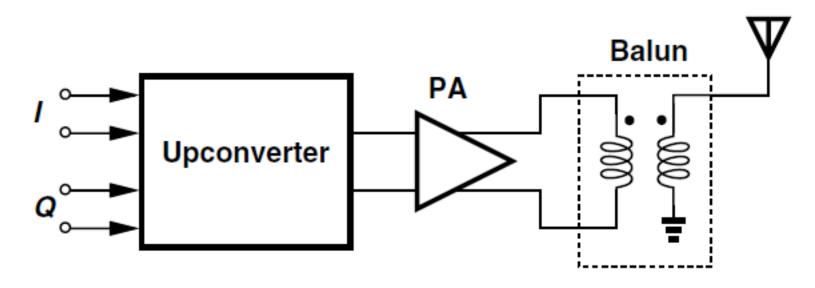
- □Single-ended PAs stems from very large transient currents that they pull from the supply to the ground
- □The resonance or impedance transformation is altered, and allows signal to travel back through the supply line
- □The ground bond wire inductance degenerates the output stage and introduces feedback

### **Differential PA**



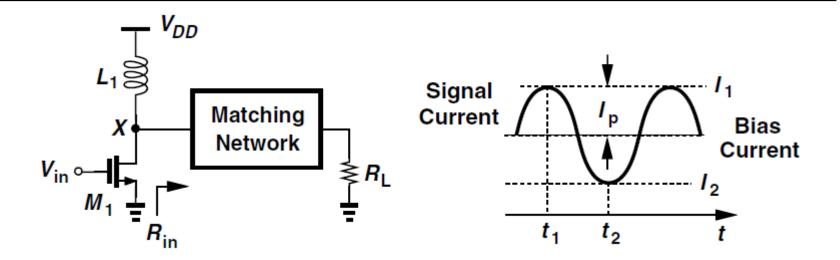
- □A differential PA draws much smaller transient currents from supply and ground lines, exhibiting less sensitivity to the bondwire inductors and creating less feedback
- ☐ The degeneration issue is also relaxed considerably

#### **Differential PA**



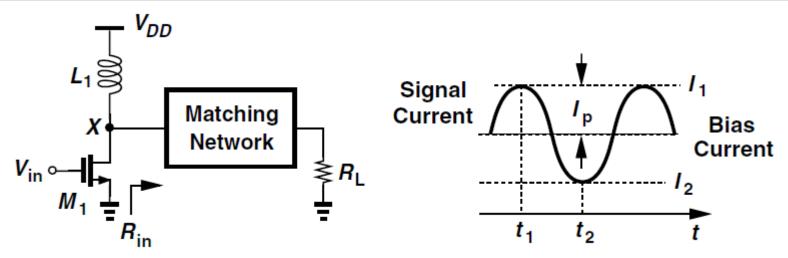
- □The use of a differential PA ameliorates both the voltage gain and package parasitic issues
- □The PA must still drive a single-ended antenna in most cases, so a balun must be inserted between PA and antenna
- □Differential PA can also reduce LO pulling by propagating symmetrically toward the LO

#### Class-A PA



- □Class-A PAs are defined as circuits in which the transistor(s) remain on and operate linearly across the full input and output range
- □The transistor bias current is chosen higher than the peak signal current
- □The input voltage should be small to ensure the linearity

# **Efficiency of Class-A PA**

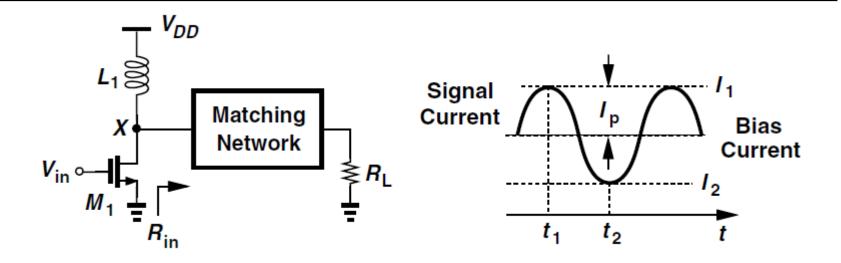


 $\Box$ To reach maximum efficiency, we allow  $V_X$  to reach  $2V_{DD}$  and nearly zero. Thus, the power delivered to the load

$$(2V_{DD}/2)^2/(2R_{in}) = V_{DD}^2/(2R_{in})$$

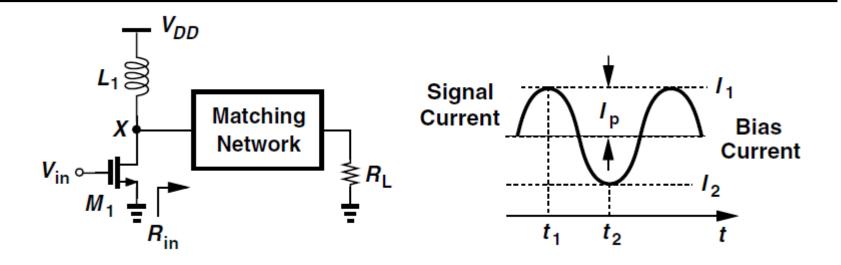
- The DC power is consumed by the constant current of  $V_{DD}/R_{in}$  from the supply voltage, so  $\eta = \frac{V_{DD}^2/(2R_{in})}{V_{DD}^2/R_{in}} = 50\%$
- □The other 50% of the supply power is dissipated by transistor

# **Efficiency of Class-A PA**



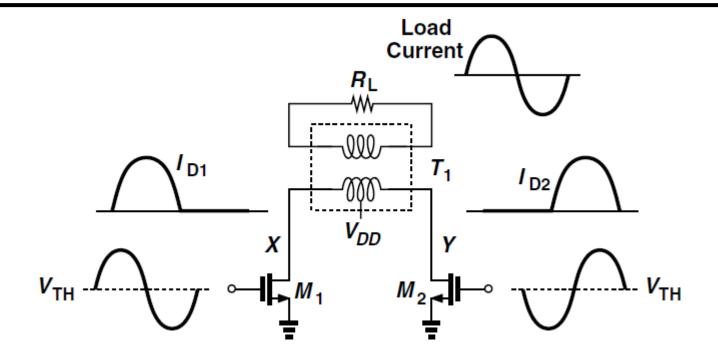
- □The assumptions lead to an efficiency of 50% in class-A PA:
- The drain peak-to-peak voltage swing is equal to twice the supply voltage with no reliability or breakdown issues
- The transistor barely turns off (tolerable nonlinearity)
- The matching network is lossless

### **Conduction Angle**



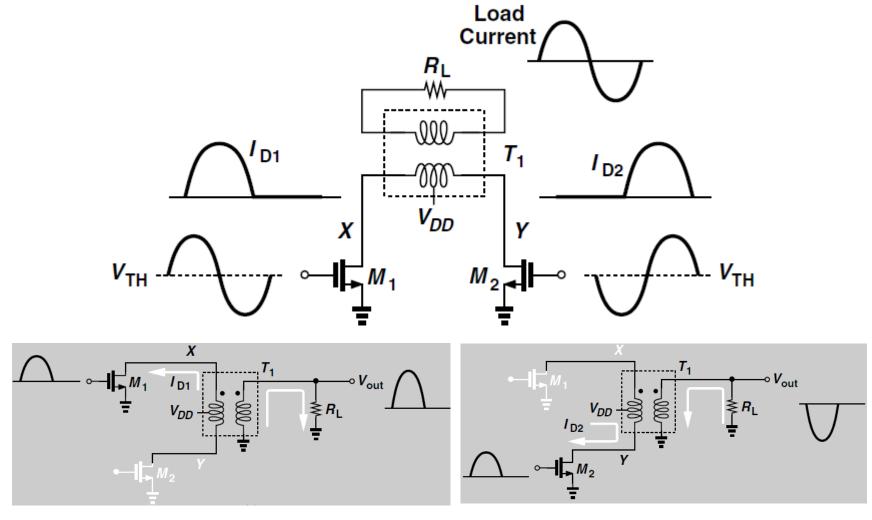
- □The conduction angle is defined as the percentage of the signal period during which the transistor(s) remain on multiplied by 360°
- □In class-A stages, the conduction angle is 360° because the output transistor is always on

#### Class-B PA

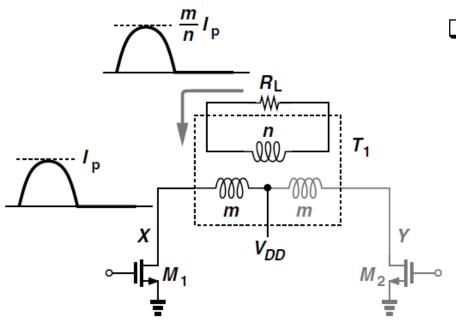


- $\Box$ The drain currents of  $M_1$  and  $M_2$  are combined by a transformer
- □ Each transistor turns off for half of period (i.e., the conduction angle is 180°)

### **Current Combine**



# **Efficiency of Class-B PA**



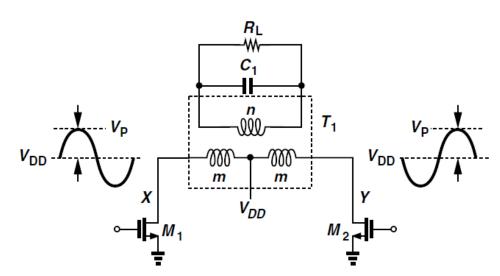
□Since two current waveforms are drawn from  $V_{DD}$  in each period, the average power provided by  $V_{DD}$  is equal to

$$P_{supp} = 2\frac{I_p}{\pi}V_{DD}$$

The transistor current  $I_{D1}=I_p \sin \omega_0 t$  produces a similar current in the load  $I_L=(m/n)I_p \sin \omega_0 t$ , producing an average power:

$$P_{out} = \left(\frac{m}{n}\right)^2 \frac{R_L I_p^2}{2} \qquad \eta = \frac{\pi}{4V_{DD}} \left(\frac{m}{n}\right)^2 I_p R_L$$

# **Efficiency of Class-B PA**



the presence □In the load, resonant transformer primary senses a voltage given by

$$V_{XY} = 2V_p \sin \omega_0 t$$

□Experiencing a ratio of n/(2m) outputs a voltage:

$$V_{out}(t) = \left(\frac{n}{2m}\right) 2V_p \sin \omega_0 t = \frac{m}{n} I_p R_L \sin \omega_0 t \qquad V_p = \frac{m^2}{n^2} I_p R_L$$

 $V_{out}(t) = \left(\frac{n}{2m}\right) 2V_p \sin \omega_0 t = \frac{m}{n} I_p R_L \sin \omega_0 t$   $V_p = \frac{m^2}{n^2} I_p R_L$   $\square \text{We choose V}_p = V_{DD} \text{ to maximize the efficiency: } \eta = \frac{\pi}{4} \approx 79\%$ 

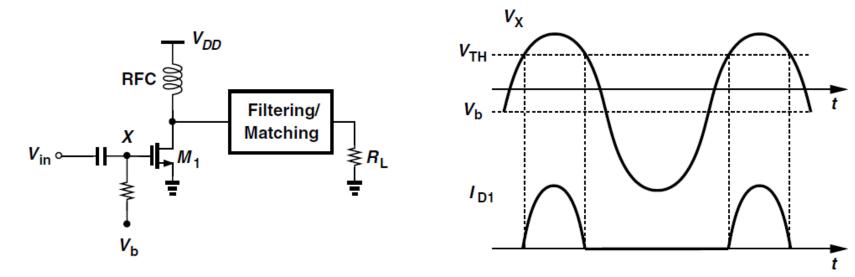
□In recent RF design literature, class B operation often refers to half of the circuits, which still has a maximum efficiency of  $\pi/4$ 

#### Class-AB PA

- □The term "class AB" is sometimes used to refer to a single-ended PA whose conduction angle falls between 180° and 360°, i.e., in which the output transistor turns off for less than half of a period
- □From another perspective, a class-AB PA is less linear than a class A stage and more linear than a class B stage
- □Class-AB PA is usually accomplished by reducing the input voltage swing and hence backing off from the 1-dB compression point

#### Class-C PA

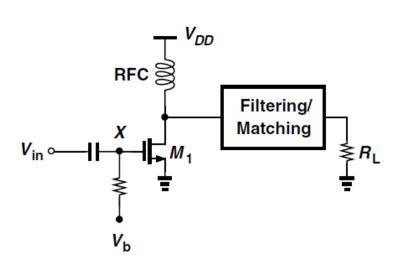
- □Class A and B stages indicates that a smaller conduction angle yields a higher efficiency
- □In class C stages, this angle is reduced further (and the circuit becomes more nonlinear)

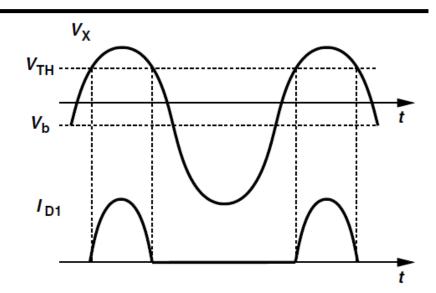


□To avoid large harmonic levels at the antenna, the input/output matching network must provide some filtering

[B. Razavi, RF Microelectronics]

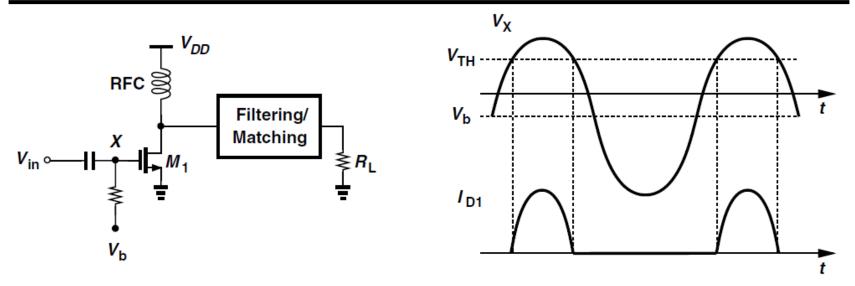
#### Class-C PA





- □The distinction between class C and one-transistor class B stages is in the conduction angle θ
- $\Box$  As  $\theta$  decreases, the transistor is on for a smaller fraction of the period, thus dissipating less power, and meanwhile the PA outputs less power

# **Efficiency of Class-C PA**



 $\Box$ If the drain current of  $M_1$  is assumed to be the peak section of a sinusoid and the drain voltage is a sinusoid having a peak amplitude of  $V_{DD}$ , then the efficiency can be obtained as

$$\eta = \frac{1}{4} \frac{\theta - \sin \theta}{\sin(\theta/2) - (\theta/2)\cos(\theta/2)}$$

**This relation suggests an efficiency of 100% as θ approaches** 

zero

# **Efficiency of Class-C PA**

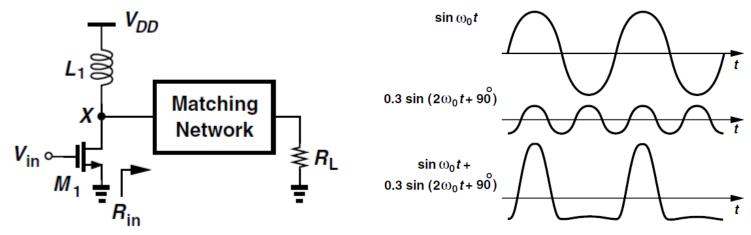
□The maximum efficiency of class-C PA is 100%, while the actual power delivered to the load:

$$P_{out} \propto \frac{\theta - \sin \theta}{1 - \cos(\theta/2)}$$

- $\Box$ The output power falls to zero as  $\theta$  approaches zero
- □In other words, a class-C PA provides a high efficiency only if it delivers a fraction of the peak output power
- □The small conduction angle dictates that the output transistor be very wide so as to deliver a high current for a short amount of time

### **Harmonic Enhanced Class-A**

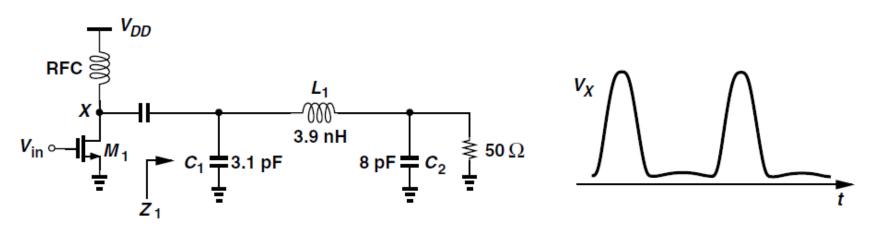
□If we minimize the time during which the transistor carries a large current and sustains a large voltage, we can reduce the power consumed by the transistor and raise the efficiency



- □The input impedance of matching network is low at the fundamental and high at the second harmonic
- □The overlap time between the voltage across and the current flowing in the output transistor is reduced

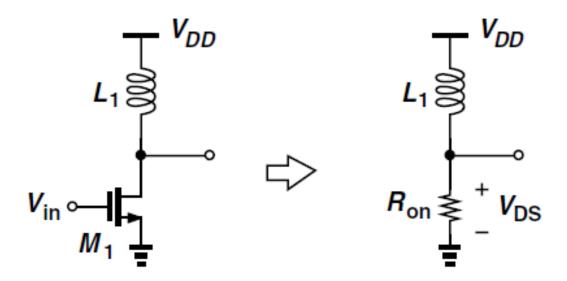
  [B. Razavi, RF Microelectronics]

### **Harmonic Enhanced Class-A**



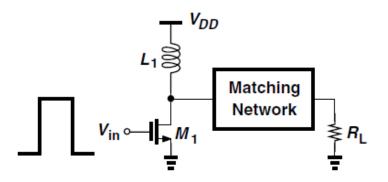
- □The technique realizes different impedances for different harmonics to make the drain voltage approach a square wave
- $\Box$ A matching network transforms the 500hm load to  $Z_1$ =90hm at f=850MHz and  $Z_2$ =3300hm at 2f=1.7GHz
- □The second harmonic is enhanced by a factor of 37, and then the PA achieves 73% efficiency

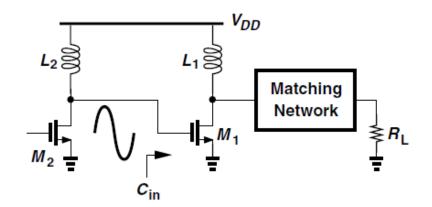
□Class-E PAs are nonlinear amplifiers that achieve efficiencies approaching 100% while delivering full power

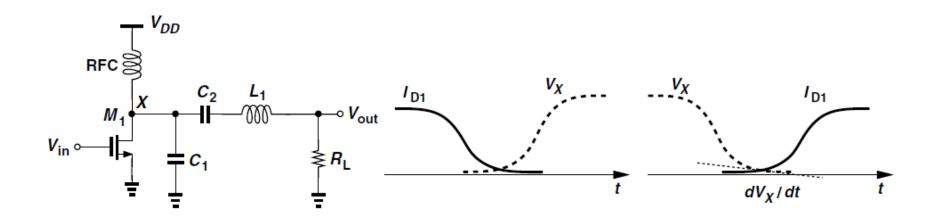


□If the transistor operates as a switch, rather than a voltage dependent current source, ideally turning on and off abruptly, resulting in a class-E PA (switching PA)

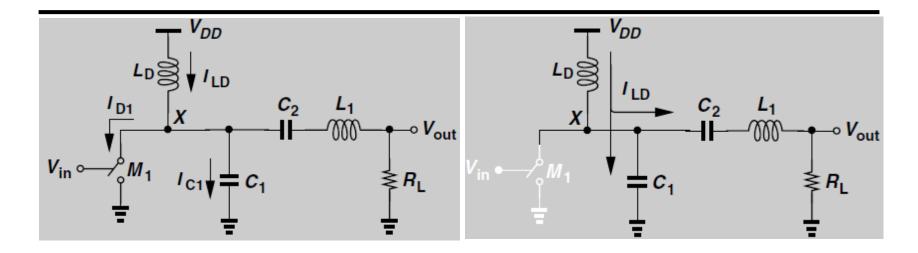
- □A serious dilemma in class-E PA design is that the gate of transistor must be switched as abruptly as possible so as to maximize the efficiency
- □But the input of transistor is usually a sinusoid waveform from previous stages



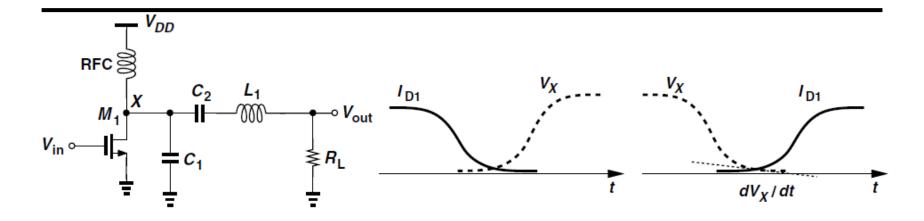




- $\Box$ As the switch turns off,  $V_x$  remains low long enough for the current to drop to zero (guaranteed by C<sub>1</sub>)
- $\Box V_x$  reaches zero just before the switch turns on, ensuring that the voltage and current of transistor do not overlap
- $\Box$ In the vicinity of the turn-on point,  $dV_x/dt$  is also near zero to lower the sensitivity to violations [B. Razavi. RF Microelectronics]



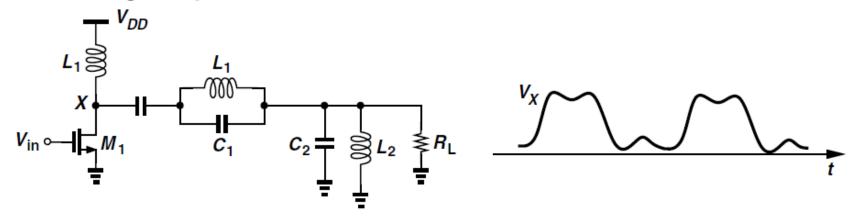
- □One half cycle is dedicated to charging L<sub>D</sub> at a small voltage V<sub>X</sub>
- $\square$ When M<sub>1</sub> turns off, the inductor current begins to flow through C<sub>1</sub>, and V<sub>x</sub> start to go up
- $\Box$ The matching network attenuates higher harmonics of  $V_X$ , yielding a nearly sinusoidal output



- □Class-E PA is quite nonlinear and exhibit a trade-off between efficiency and output harmonic content
- □Class-E PA sustains a large peak voltage in the off state, raising serious device reliability or breakdown issues

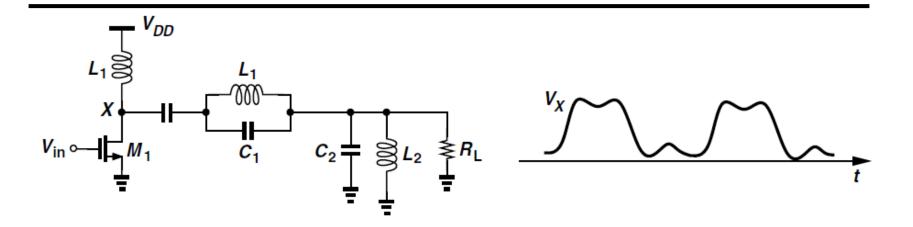
#### Class-F PA

□If the load network provides a high termination impedance at the second or third harmonics, the voltage waveform across the switch exhibits sharper edges than a sinusoid, thereby reducing the power loss in the transistor



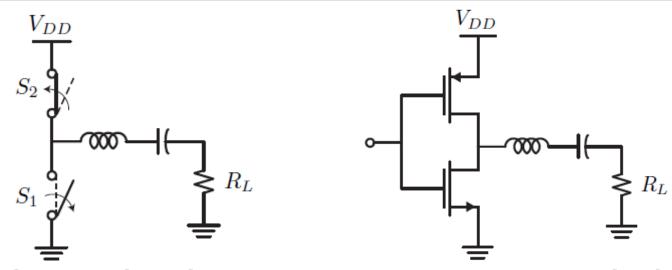
 $\Box$ The tank consisting of L<sub>1</sub> and C<sub>1</sub> resonates at three times the input frequency, and then V<sub>X</sub> approaches a rectangular waveform with the addition of the third harmonic

#### Class-F PA



□If the drain current of the transistor is assumed to be a half-wave rectified sinusoid, it can be proved that the peak efficiency of class F amplifiers is equal to 88% for third harmonic peaking

#### Class-D PA



- □If give up linearity, then we can create some intrinsically efficient amplifiers using switches. An ideal switch does not dissipate any power since either the voltage or current is zero
- □MOS transistors make particularly good switches. The input voltage should be large enough
- □A series LCR filter only allows the first harmonic of voltage to flow into the load

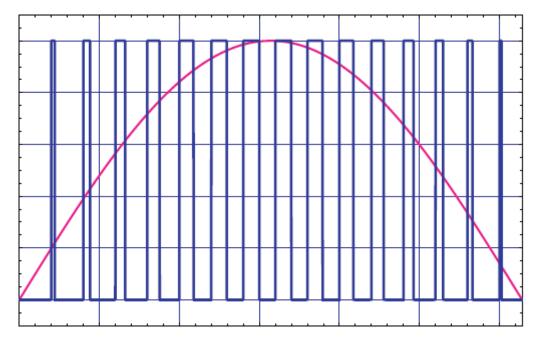
  [Ali Niknejad, EE142 & EE242 of UC Berkeley]

### **Efficiency of Class-D PA**

- □We can see that the efficiency has to be 100% for an ideal switch. That's because there is no where for the DC power to flow except to the load
- □The real efficiency is lowered by the switch-on resistance
- □We can make our switches bigger to minimize the resistance, but this in turn increases the parasitic capacitance
- □There are two forms of loss associated with the parasitic capacitance, the capacitor charging losses CV<sup>2</sup>f and the parasitic substrate losses
- $\Box$ The power required to drive the switches also increases proportional to  $C_{gs}$  since we have to burn  $CV^2f$  power to drive the inverter

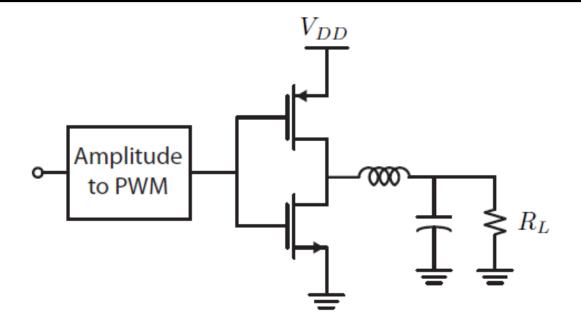
[Ali Niknejad, EE142 &EE242 of UC Berkeley]

#### Class-S PA



- □If the switching rate is much higher than the fundamental, then amplitude modulation can be converted to pulse-width modulation
- □A low-pass filter at the output faithfully recreates the envelope of the signal

#### Class-S PA



- □Class S amplifiers are commonly used at low frequencies (audio) since the transistors can be switched at a much higher frequency than the fundamental
- □This allows efficiencies approaching 100% with good linearity

[Ali Niknejad, EE142 &EE242 of UC Berkeley]

# **Efficiency Summary**

Typology	Efficiency
Class A	50%
Harmonic Enhanced Class A	~73%
Class B	79%
Class AB	50%-79%
Class C	~100%
Class E	~100%
Class F	~88%
Class D	~100%
Class S	~100%